## IN THE ABSTRACT

Amend the abstract as follows:

A semiconductor junction varactor <u>is designed with utilizes</u> gate enhancement for enabling the varactor to achieve a high ratio of maximum capacitance to minimum capacitance. The varactor has a gate region (131 or 181) divided into multiple portions of differing zero-point threshold voltages for enabling the varactor capacitance to vary relatively gradually with a control voltage applied to the varactor.

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